

Features

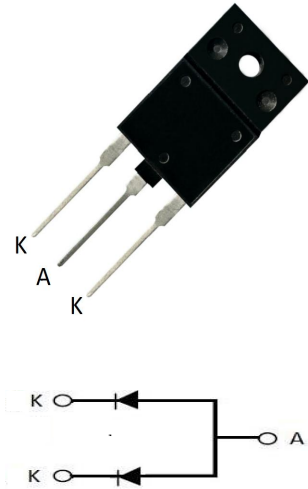
- Adopt FRED chip
- Low forward Voltage drop
- Fast reverse recovery time
- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability

Typical Applications

- Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

Mechanical Data

- **Package:** TO-247F-3L
Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant
- **Terminals:** Tin plated leads, solderable per J-STD-002 and JESD22-B102
- **Polarity:** As marked



	V_{RSM} V	V_{RRM} V
MUR6060PTR	600	600

■Maximum Ratings ($T_j=25^{\circ}\text{C}$ Unless otherwise specified)

Symbol	Parameter		Value	Unit	
V_{RRM}	Repetitive peak reverse voltage		600	V	
$I_{F(RMS)}$	RMS forward voltage		60	A	
$I_{F(AV)}$	Average forward current $\delta = 0.5$	$T_c = 125^{\circ}\text{C}$	Per diode	30	A
		$T_c = 110^{\circ}\text{C}$	Per device	60	
		$T_c = 100^{\circ}\text{C}$	Per diode	40	
		$T_c = 80^{\circ}\text{C}$	Per device	80	
I_{FSM}	Surge non repetitive forward current	$t_p = 10\text{ms}$ sinusoidal	300	A	
T_{stg}	Storage temperature range		-65 to + 175	$^{\circ}\text{C}$	
T_j	Maximum operating junction temperature		175	$^{\circ}\text{C}$	

Symbol	Parameter		Value (max).	Unit
$R_{th(j-c)}$	Junction to case	Per diode	1.05	$^{\circ}\text{C}/\text{W}$
		Total	0.68	
$R_{th(c)}$	Coupling		0.3	$^{\circ}\text{C}/\text{W}$

When the diodes 1 and 2 are used simultaneously:
 $\Delta T_j(\text{diode } 1) = P(\text{diode } 1) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode } 2) \times R_{th(c)}$

■Electrical Characteristics

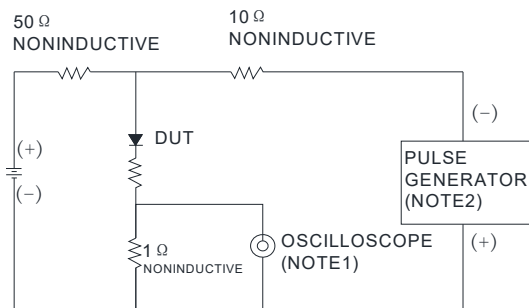
Symbol	Parameter	Test conditions		Min.	Typ	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			25	μA
		$T_j = 150^\circ\text{C}$			80	800	
V_F^{**}	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 30\text{A}$			1.55	V
		$T_j = 150^\circ\text{C}$			1.0	1.25	
		$T_j = 25^\circ\text{C}$	$I_F = 60\text{A}$			1.75	
		$T_j = 150^\circ\text{C}$			1.24	1.55	

Pulse test: * $t_p = 5\text{ ms}$, $\delta < 2\%$
 ** $t_p = 380\ \mu\text{s}$, $\delta < 2\%$

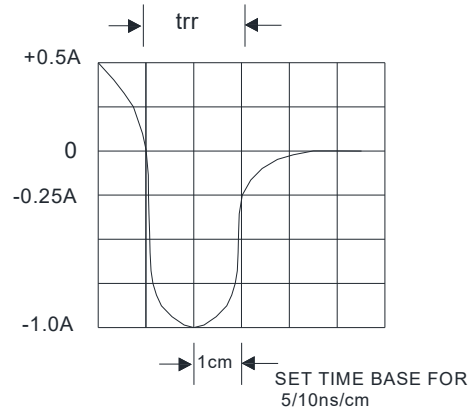
To evaluate the conduction losses use the following equation: $P = 0.95 \times I_F(\text{AV}) + 0.010 I_F^2(\text{RMS})$

Symbol	Parameter	Test conditions		Min.	Typ	Max.	Unit
t_{rr}	Reverse recovery time	$T_j = 25^\circ\text{C}$	$I_F = 0.5\text{A}$ $I_{rr} = 0.25\text{A}$ $I_R = 1\text{A}$			50	ns
			$I_F = 1\text{A}$, $V_R = 30\text{V}$, $di/dt = -200\text{A}/\mu\text{s}$		30	40	
I_{RM}	Reverse recovery current	$T_j = 125^\circ\text{C}$	$I_F = 30\text{A}$ $V_R = 400\text{V}$ $di_F/dt = 100\text{A}/\mu\text{s}$		11.5	16	A
t_{fr}	Forward recovery time	$T_j = 25^\circ\text{C}$	$I_F = 30\text{A}$ $di_F/dt = 100\text{A}/\mu\text{s}$ $V_{FR} = 1.1 \times V_{Fmax}$			500	ns
V_{FP}	Forward recovery voltage	$T_j = 25^\circ\text{C}$	$I_F = 30\text{A}$ $di_F/dt = 100\text{A}/\mu\text{s}$ $V_{FR} = 1.1 \times V_{Fmax}$		2.5		V

FIG.5: Diagram of circuit and Testing wave form of reverse recovery time



NOTES:
 1. Rise Time=7ns max .Input Impedance=1M Ω 22pf
 2. Rise Time=10ns max.Source Impedance=50 Ω



■ Characteristics(Typical)

Figure 1: Conduction losses versus average forward current (per diode)

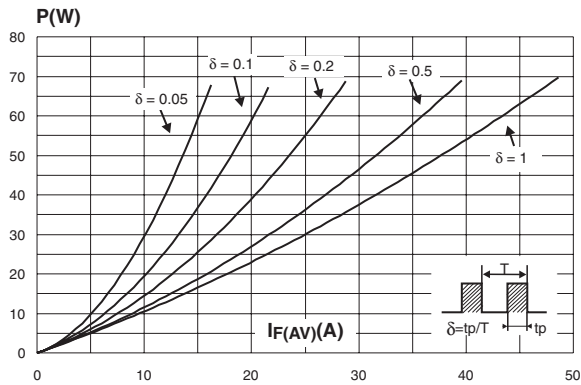


Figure 3: Relative variation of thermal impedance junction to case versus pulse duration

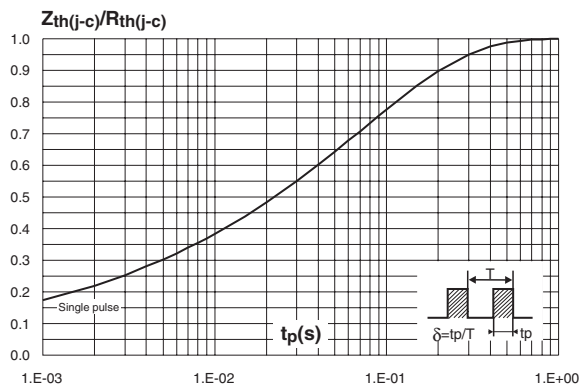


Figure 5: Reverse recovery time versus di/dt (typical values, per diode)

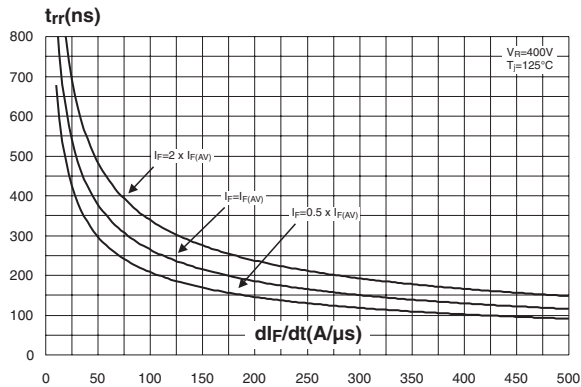


Figure 2: Forward voltage drop versus forward current (per diode)

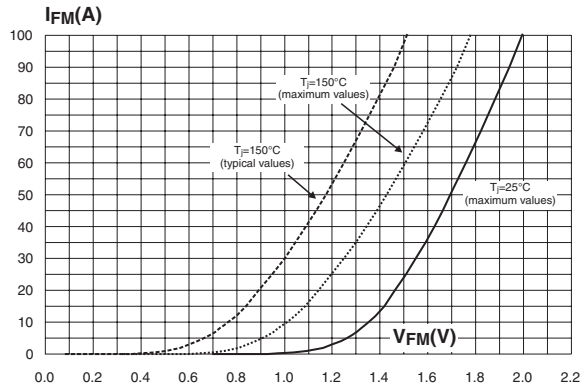


Figure 4: Peak reverse recovery current versus di/dt (typical values, per diode)

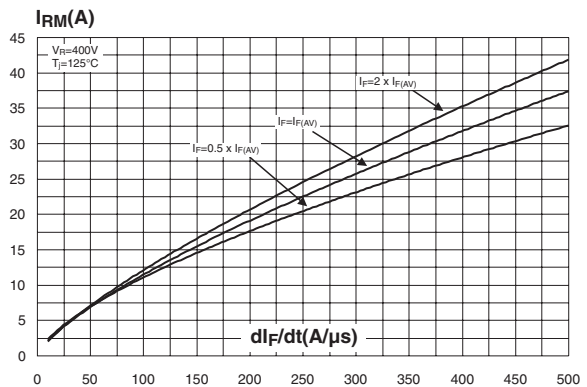
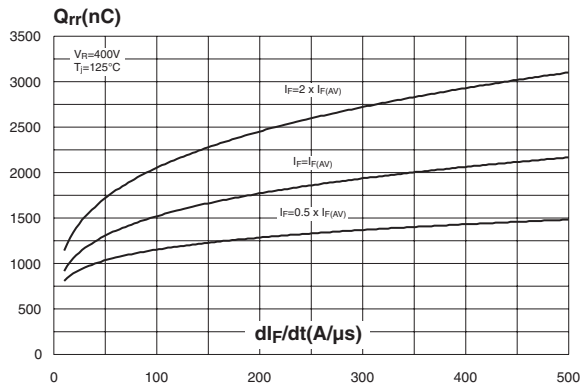


Figure 6: Reverse recovery charges versus di/dt (typical values, per diode)





MUR6060PTR

Ultra-Fast Recovery Diodes 30A*2 FRED Pt



Figure 7: Reverse recovery softness factor versus di_F/dt (typical values, per diode)

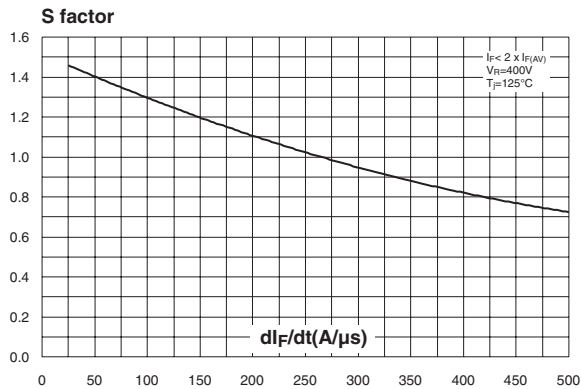


Figure 8: Relative variations of dynamic parameters versus junction temperature

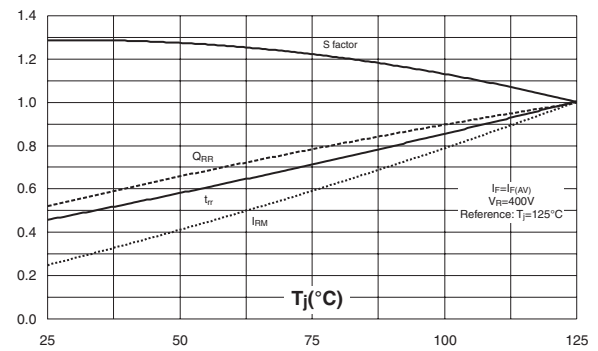


Figure 9: Transient peak forward voltage versus di_F/dt (typical values, per diode)

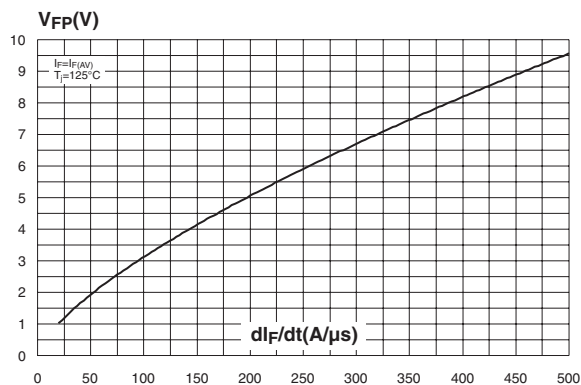


Figure 10: Forward recovery time versus di_F/dt (typical values, per diode)

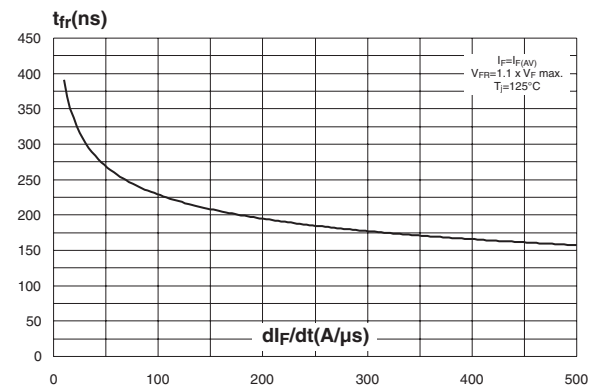
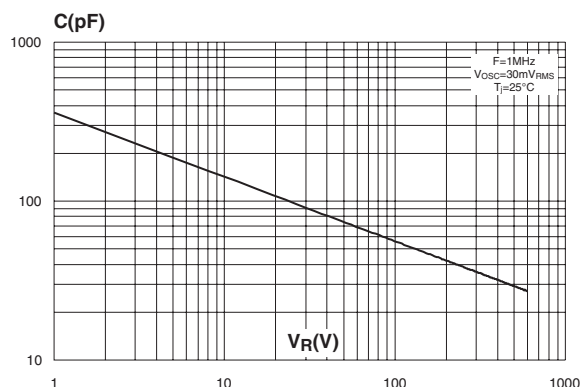
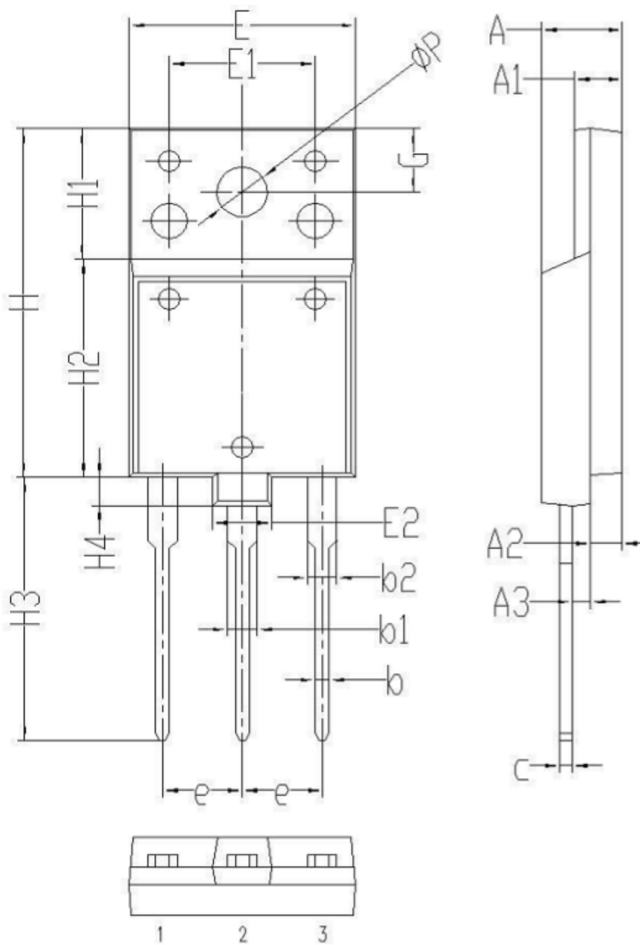


Figure 11: Junction capacitance versus reverse voltage applied (typical values, per diode)



Package Information

TO-247F-3L PACKAGE



Symbol	Unit mm		
	Min	Typ	Max
A	5.35	5.55	5.75
A1	2.80	3.00	3.20
A2	1.90	2.10	2.30
A3	1.10	1.30	1.50
b	0.65	0.75	0.85
b1	1.80	2.00	2.20
b2	1.80	2.00	2.20
c	0.70	0.90	1.10
e	5.25	5.45	5.65
E	15.3	15.5	15.7
E1	9.80	10.0	10.2
E2	3.80	4.00	4.20
H	24.3	24.5	24.7
H1	9.00	9.20	9.40
H2	15.1	15.3	15.5
H3	18.5	19.0	19.5
H4	1.80	2.00	2.20
H5	4.80	5.00	5.20
G	4.3	4.5	4.7
ΦP	3.40	3.60	3.80